

Ka Band Point Contact Detector Diodes

Point Contact Diodes: 1N Series

Description

The 1N series of Point Contact Detector diodes is designed for applications through Ka-Band. These diodes employ epitaxial silicon optimized for high tangential signal sensitivity (TSS), and are suitable for use in waveguide, coaxial and stripline applications. Being point contact diodes, they are efficient detectors not requiring the use of bias. Devices in this series are available in glass or cartridge packaging.

Features

- Broadband Operations
- Bias Not Required

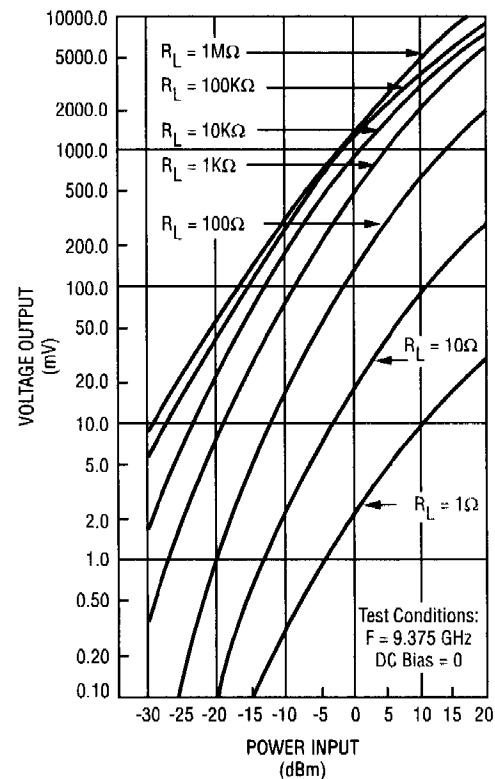
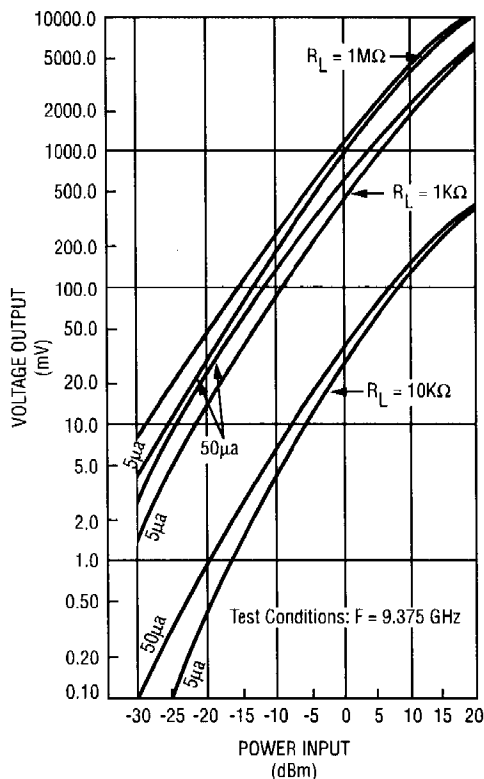
Packaging

- Glass or Cartridge

Applications

This 1N series of Point Contact Detectors is suitable for use in waveguide, coaxial and stripline applications

Typical Performance



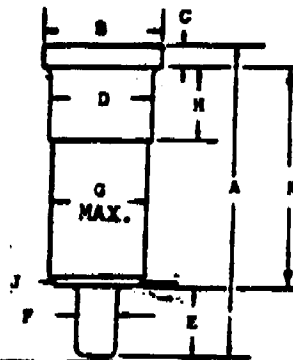
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Electrical Characteristics

Rectification Efficiency MIN	Tangential Signal Sensitivity (-dBm)	Video Resistance MAX (K Ohms)	Operating Frequency (MHz)	Case Style	Part Number
65%	-	-	100	CS85	1N830
65% @ 5 vdc	-	-	100	CS85	1N830A
-	49	22	3000	CS100	1N32
-	47	17	3000	CS100	1N32A
-	40	18	9375	CS85	1N833
-	45	18	9375	CS85	1N833A
-	51	3.1	9000	CS100	1N1611
-	53	3.1	9000	CS100	1N1611A
-	53	3.1	9000	CS100	1N1611B
-	50	10	9375	CS101	1N3778

Maximum Ratings

Operating Temperature: -55°C to + 150°C
 Storage Temperature: -65°C to + 200°C



	A	B	C	D	E	F	G	H	J	K
P3	.800	.292	.082	.244	.180	.092	.240	.192	.182	.630
	.840	.296		.280	.190	.092		.192	.228	.680